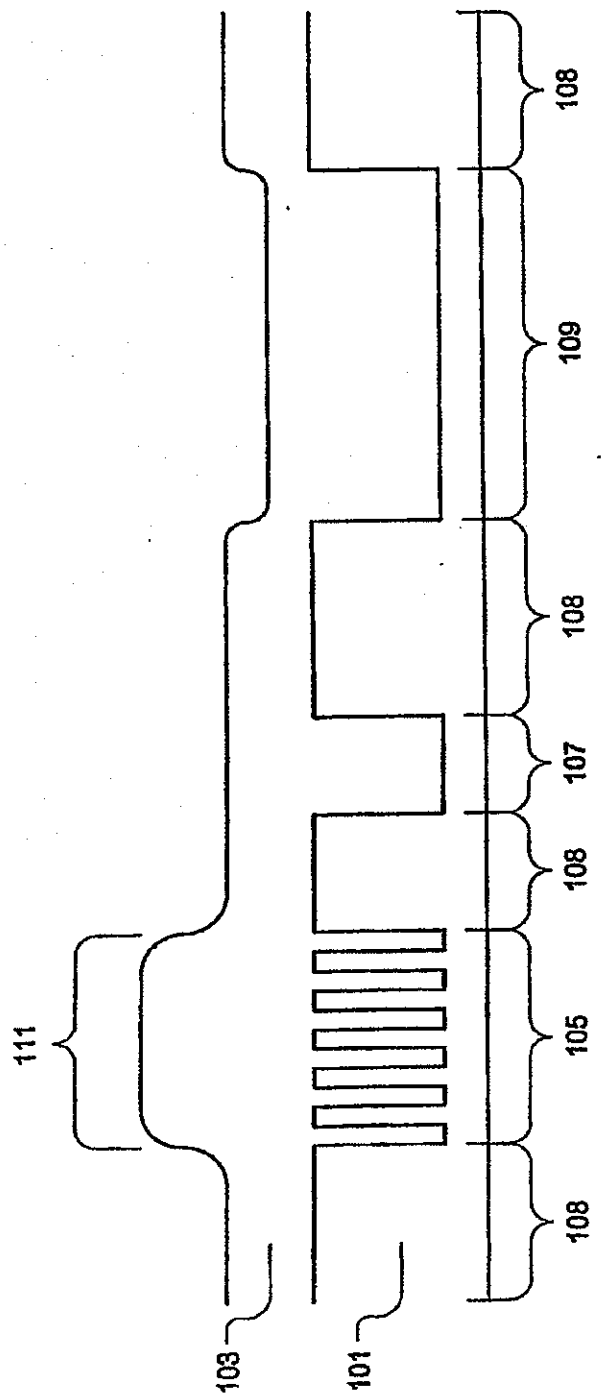


Fig. 1

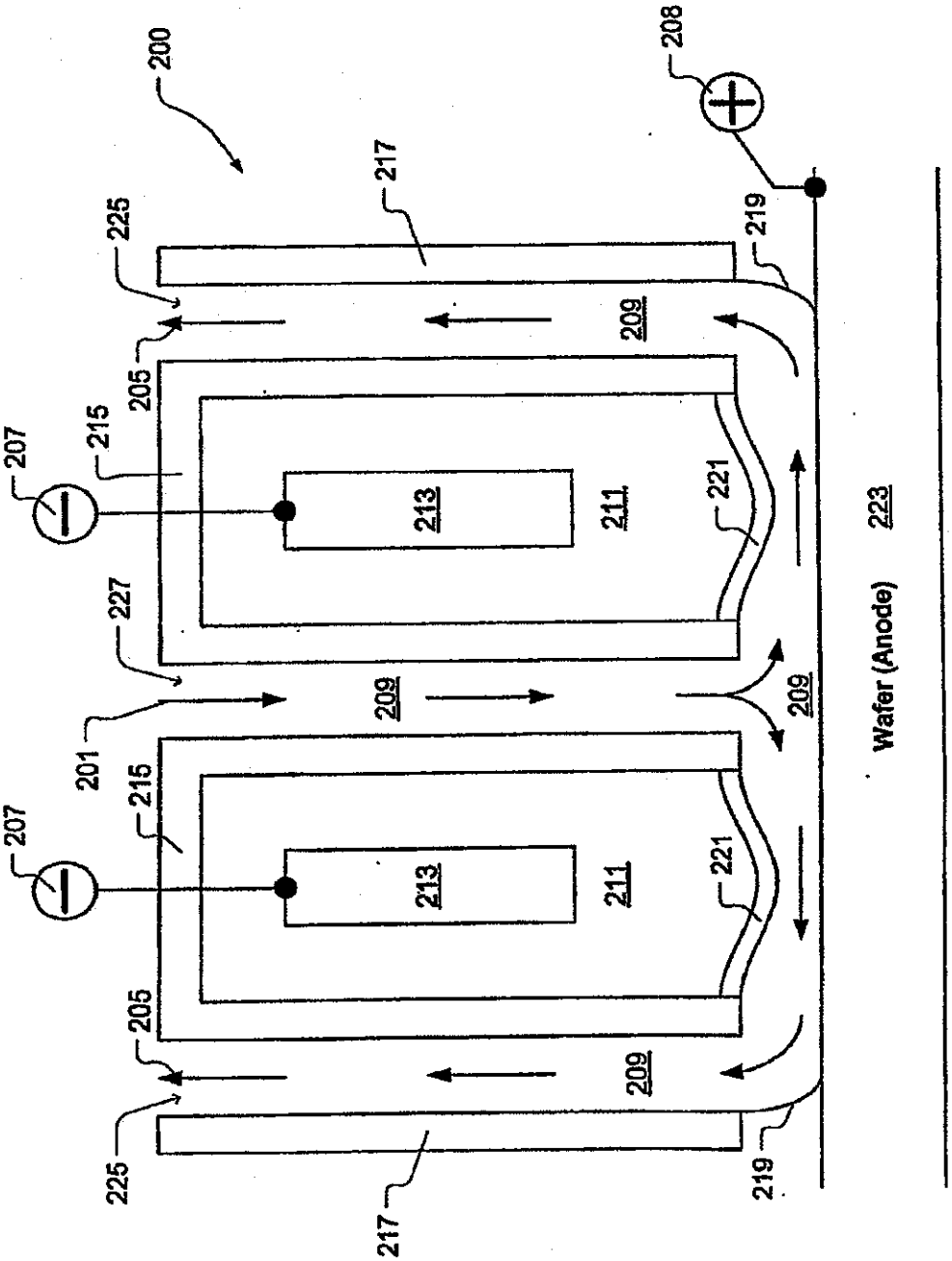

200
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217
225
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205
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213
211
221
227
201
Wafer (Anode)
223

Fig. 2A

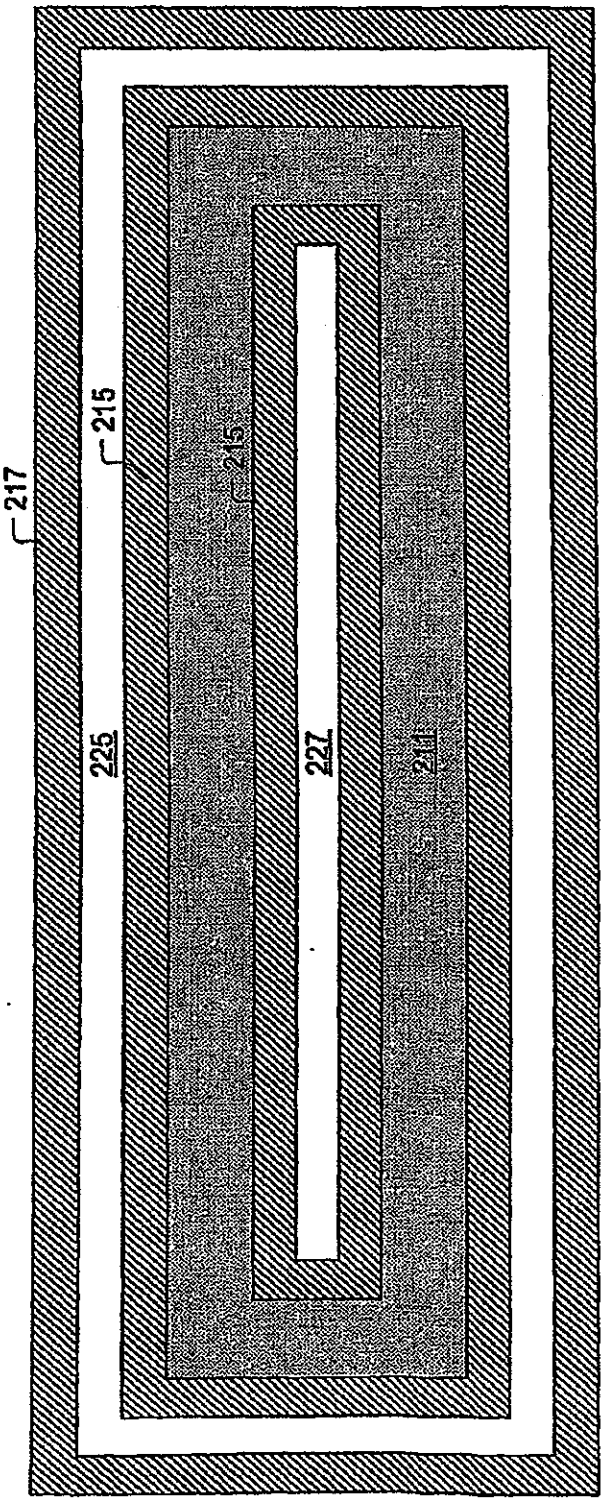


Fig. 2B

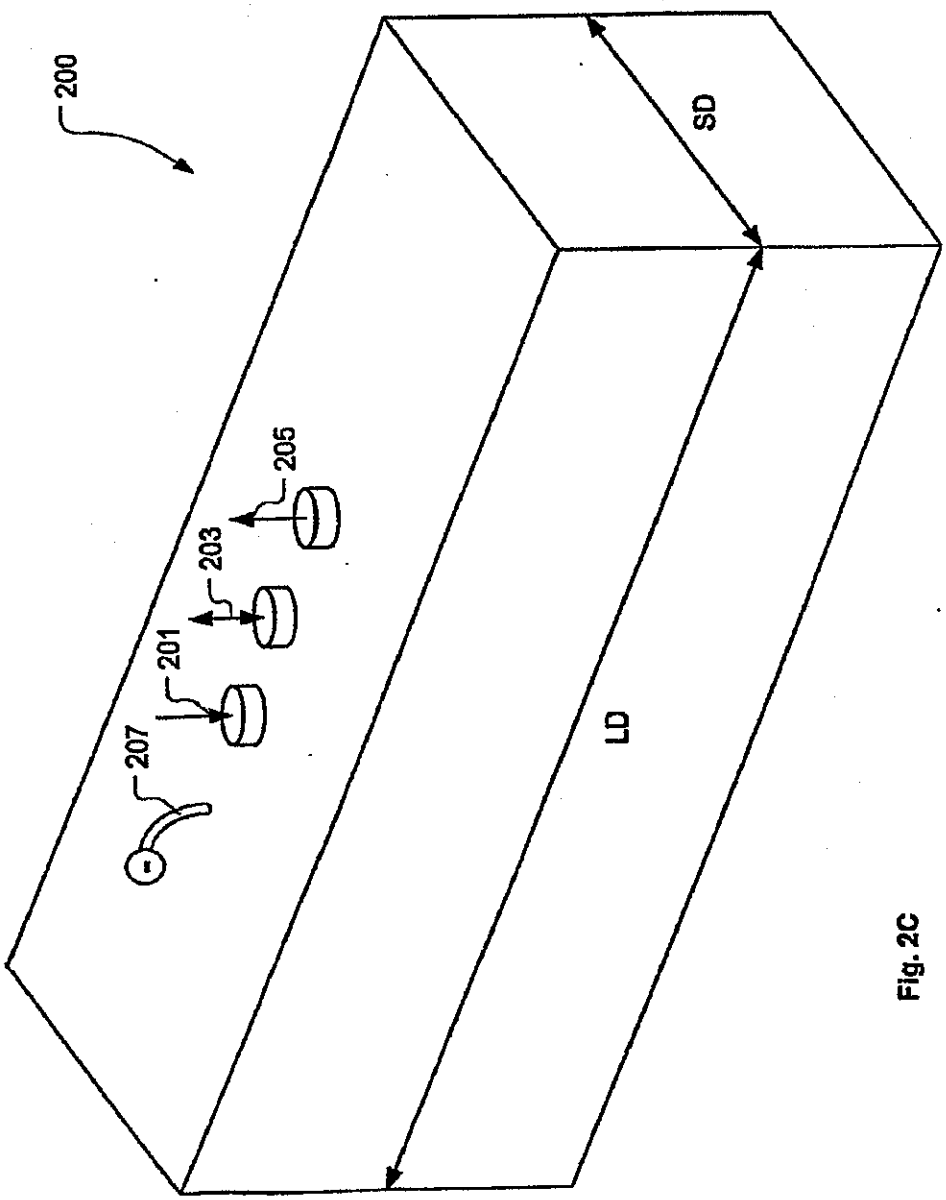


Fig. 2C

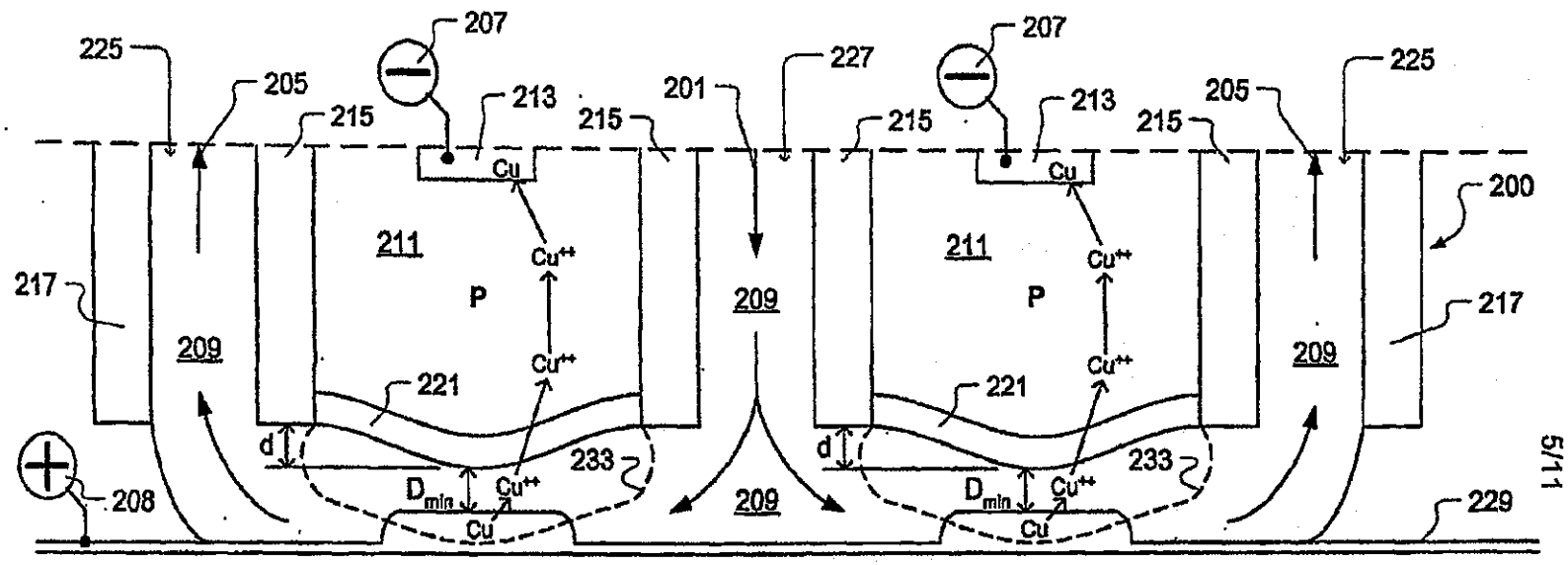

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233
d
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Cu
Cu++
208
200
229
Wafer (Anode) 223

Fig. 2D

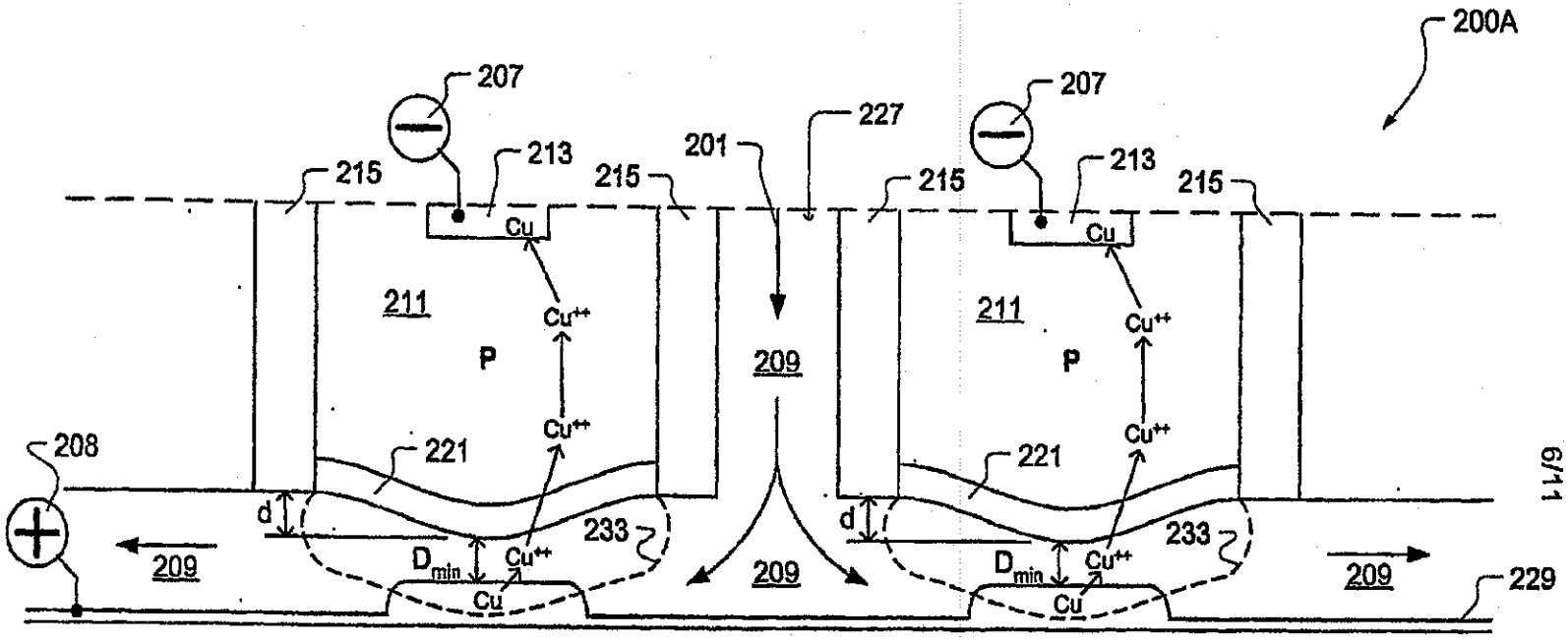

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Cu++
Cu++
Cu++
Cu++
208
221
221
d
d
233
233
209
209
209
D_{min}
D_{min}
Cu++
Cu++
Cu
Cu
229
Wafer (Anode) 223

Fig. 2E

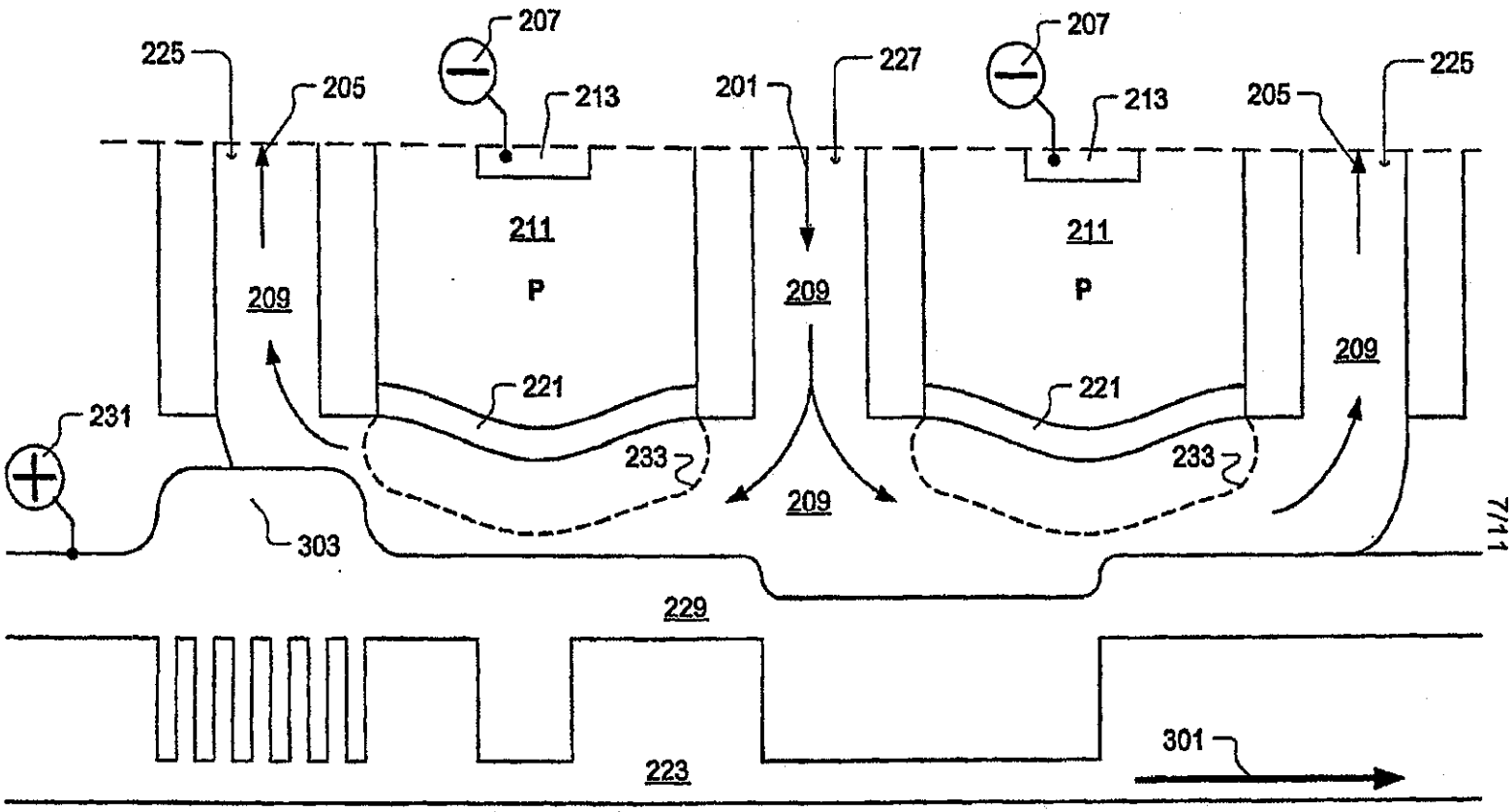

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Fig. 3A

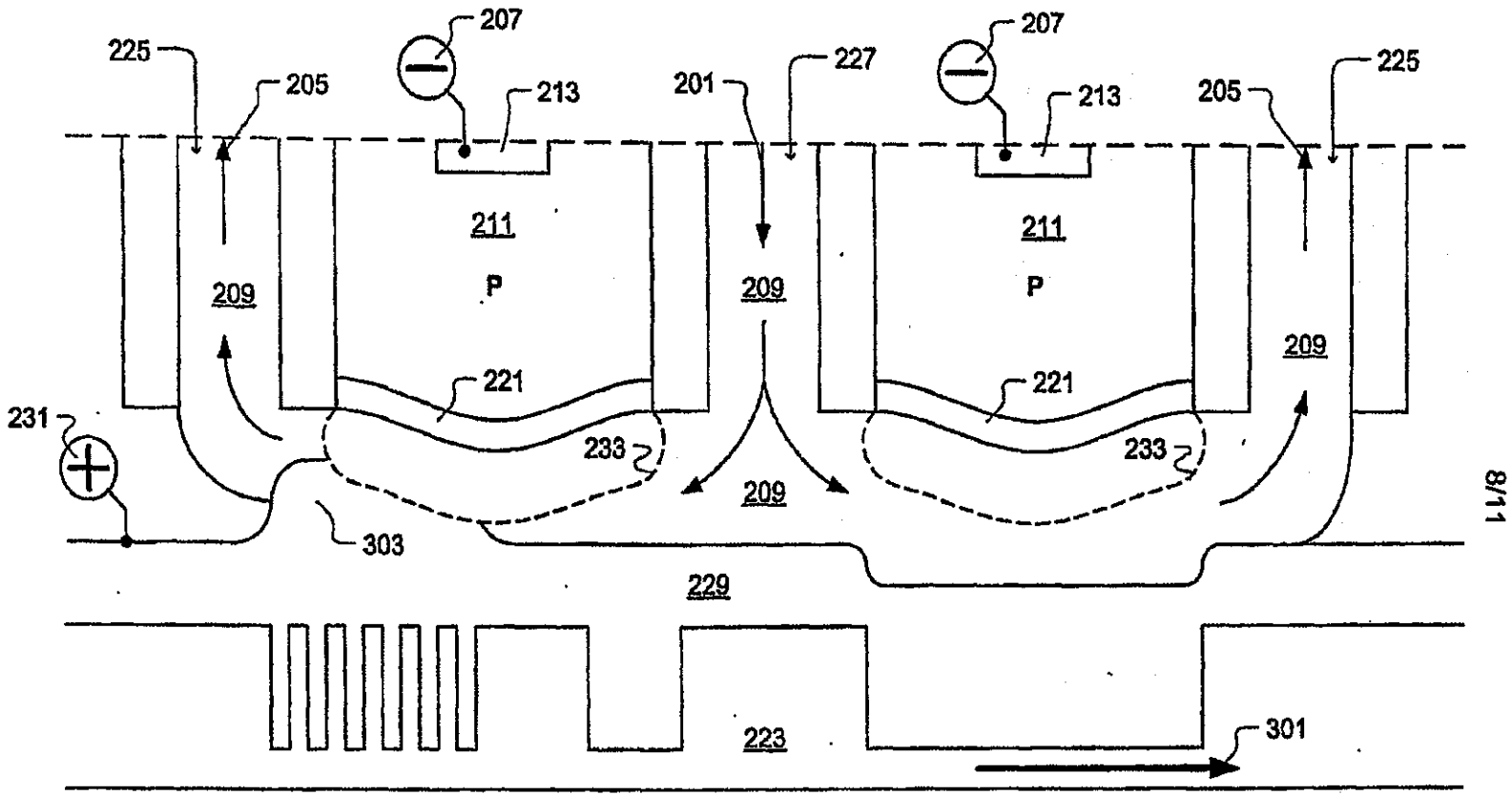

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Fig. 3B

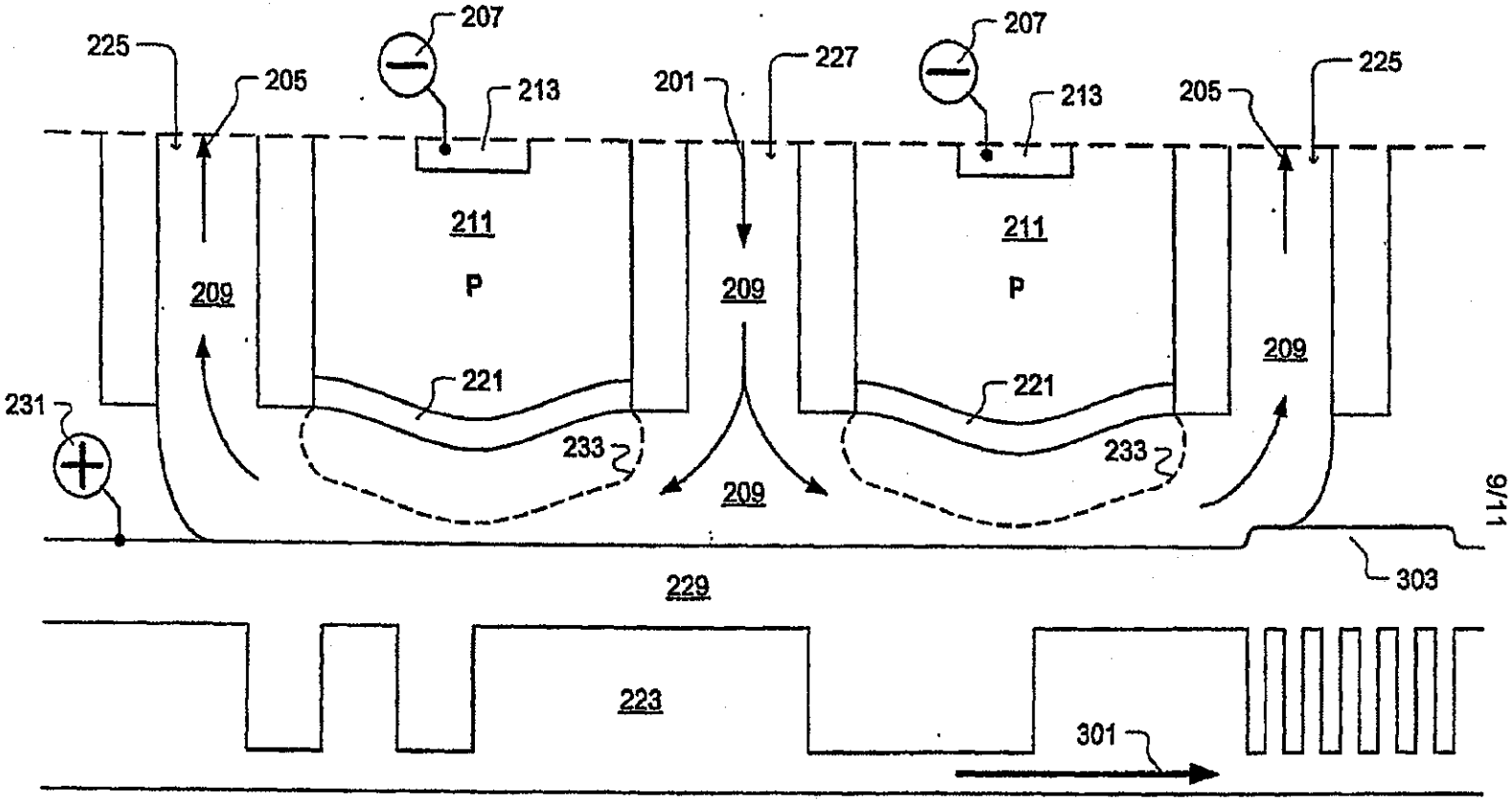

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Fig. 3C

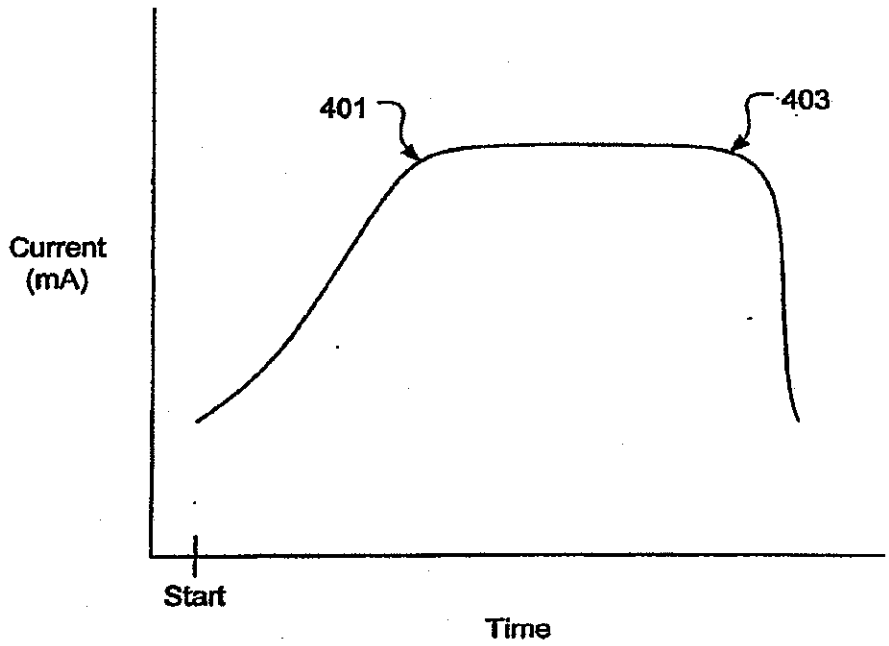


Fig. 4

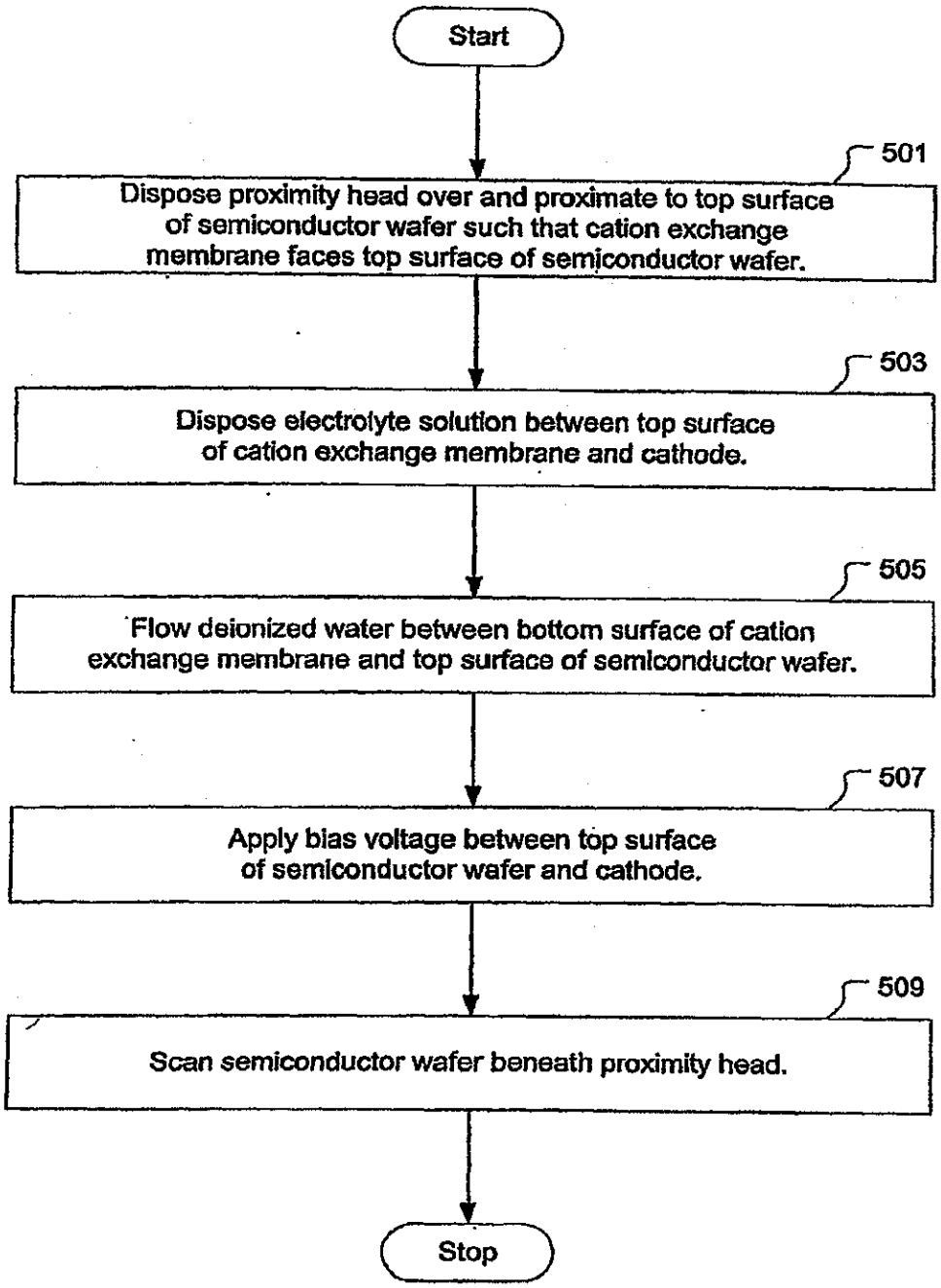

Start
501
Dispose proximity head over and proximate to top surface of semiconductor wafer such that cation exchange membrane faces top surface of semiconductor wafer.
503
Dispose electrolyte solution between top surface of cation exchange membrane and cathode.
505
Flow deionized water between bottom surface of cation exchange membrane and top surface of semiconductor wafer.
507
Apply bias voltage between top surface of semiconductor wafer and cathode.
509
Scan semiconductor wafer beneath proximity head.
Stop

Fig. 5